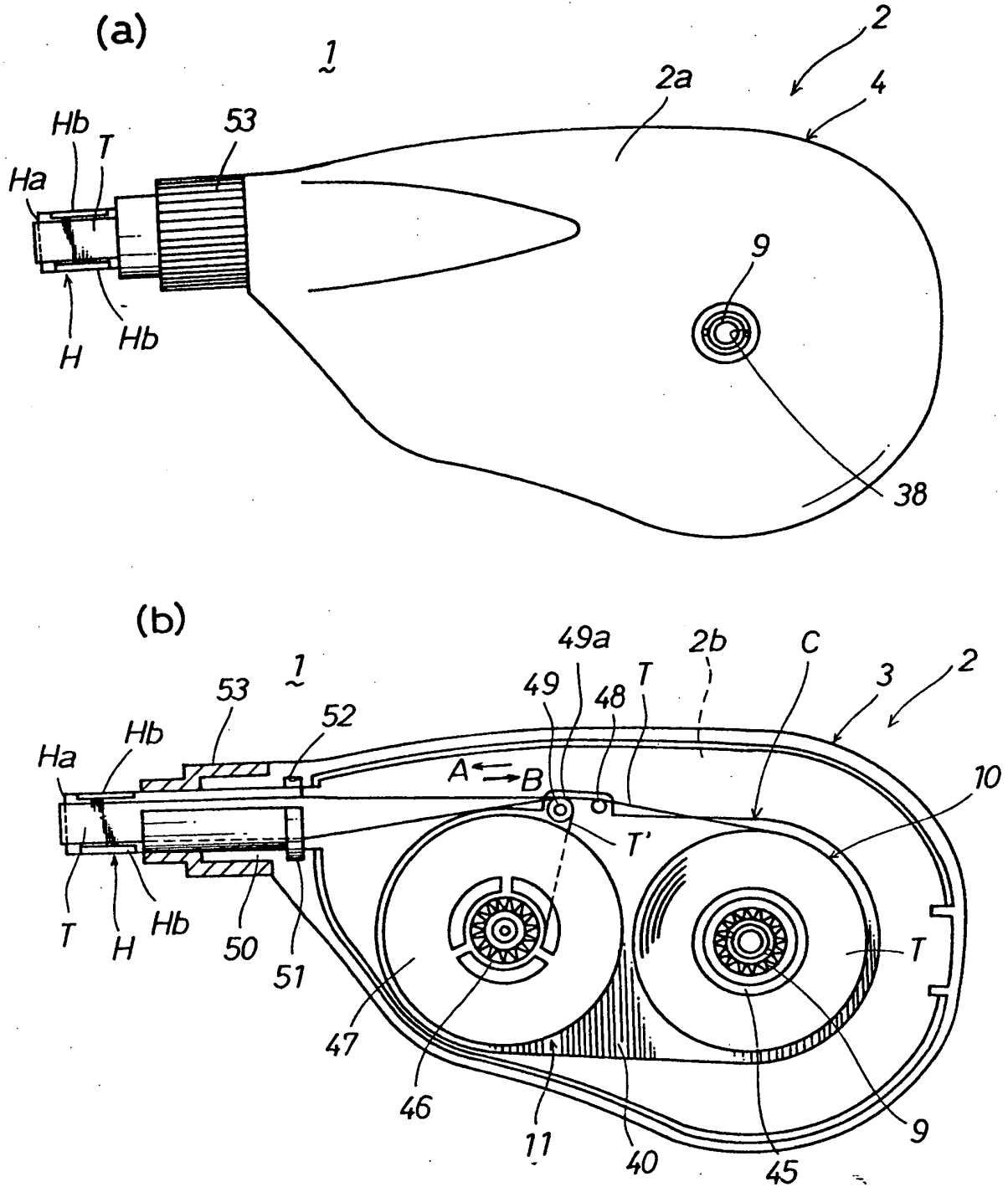


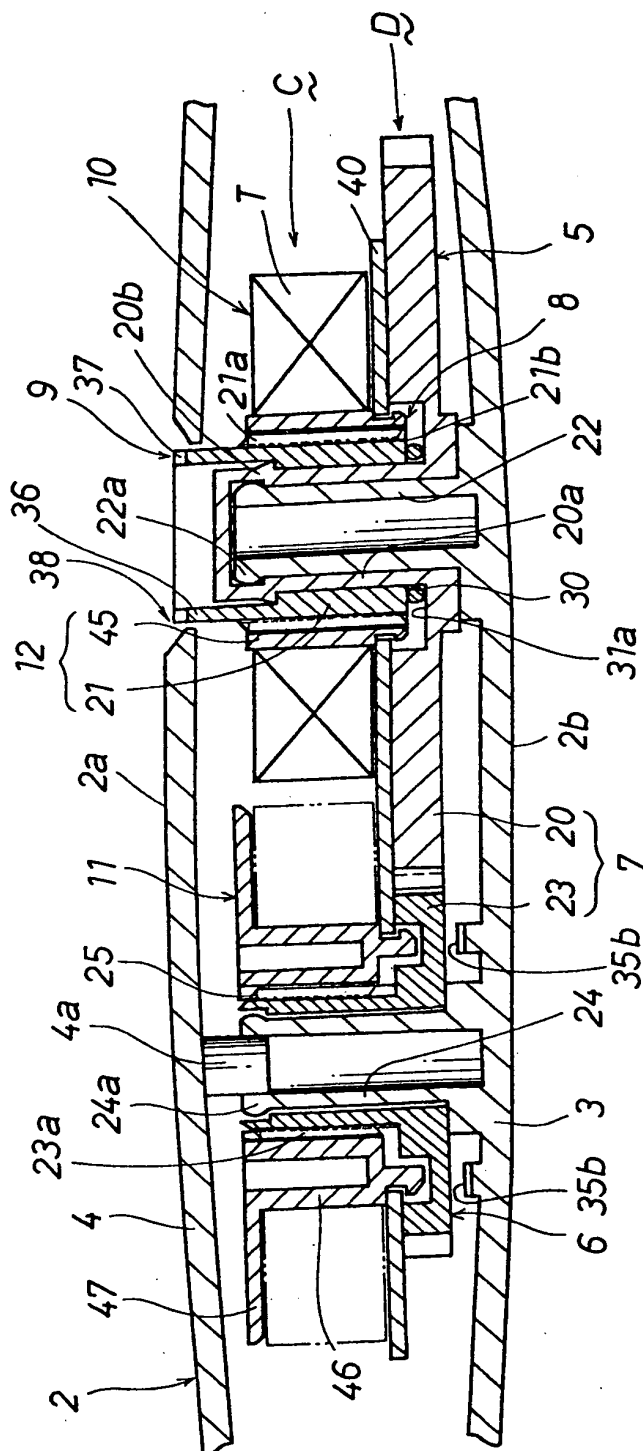
FIG. 1



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FIG.2



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FIG.3

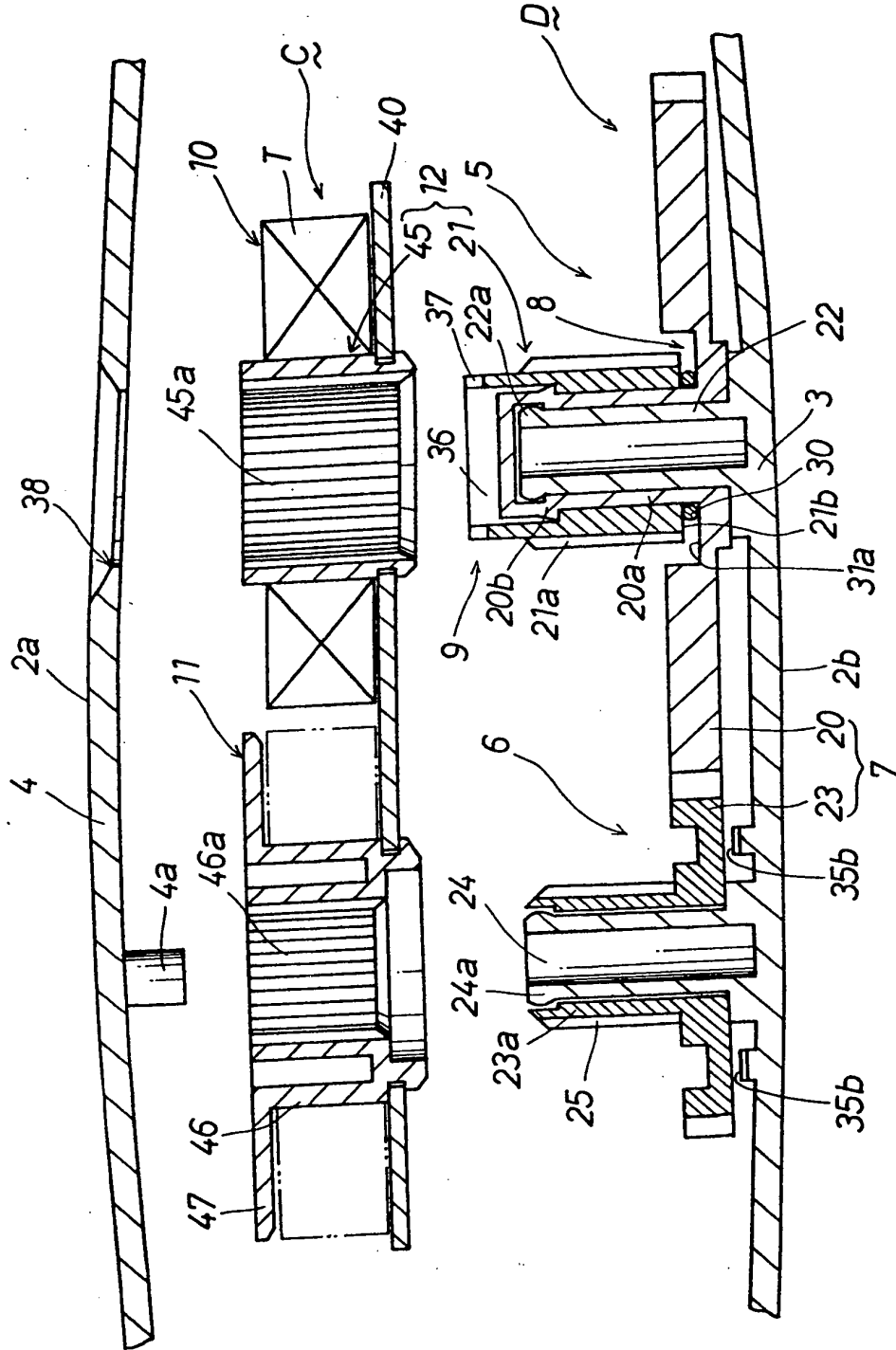
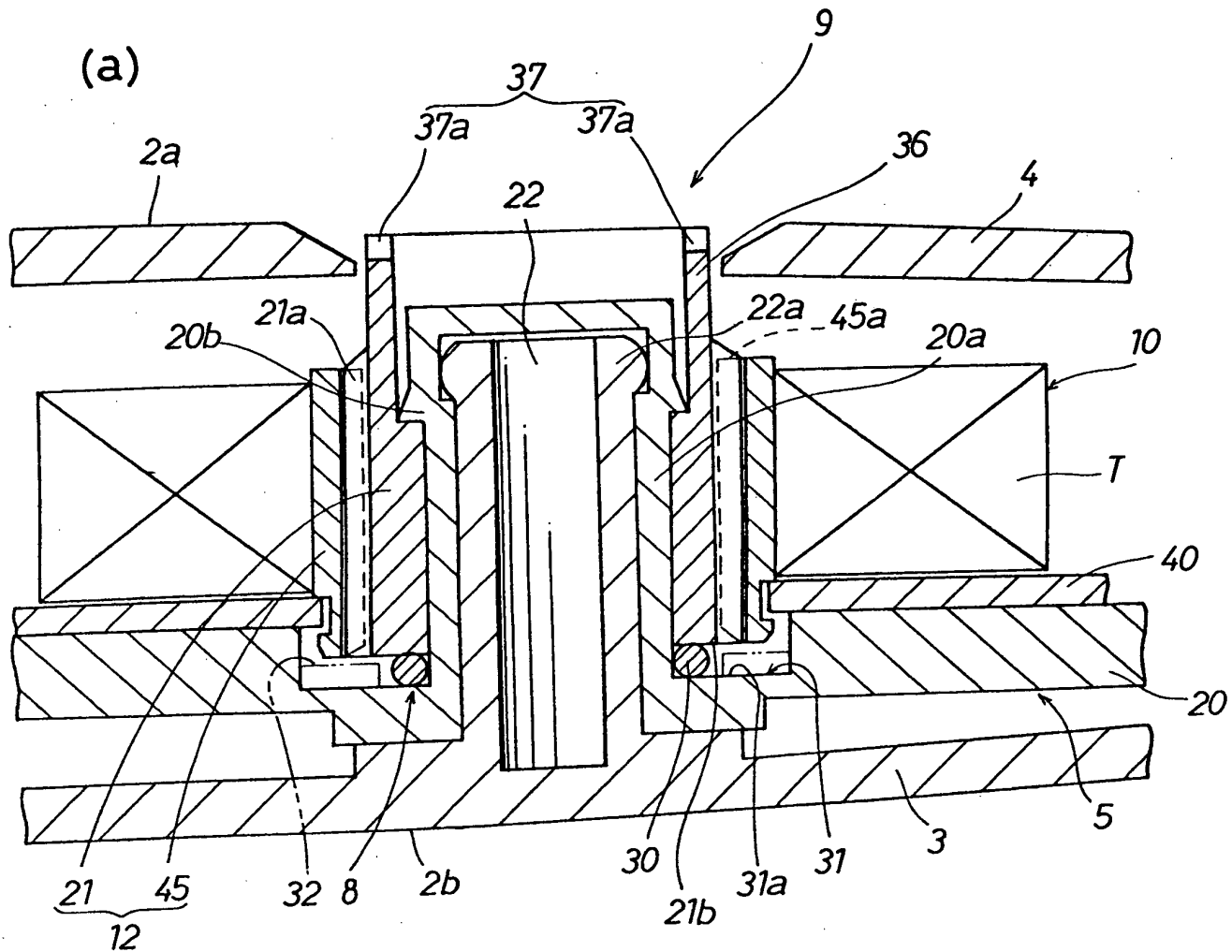


FIG. 4



(b)

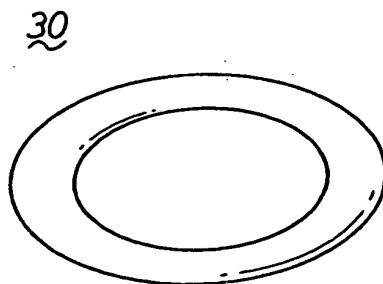
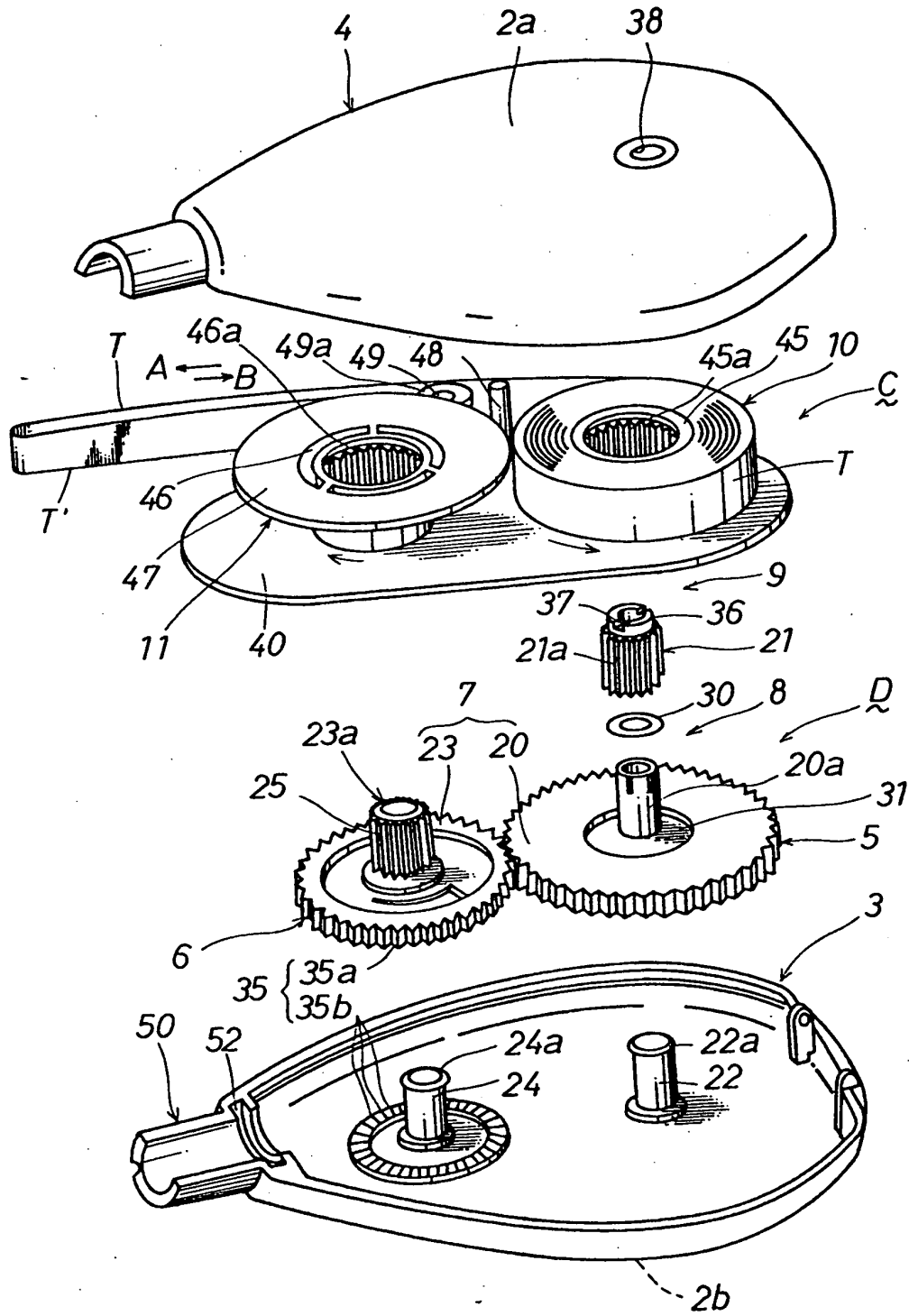
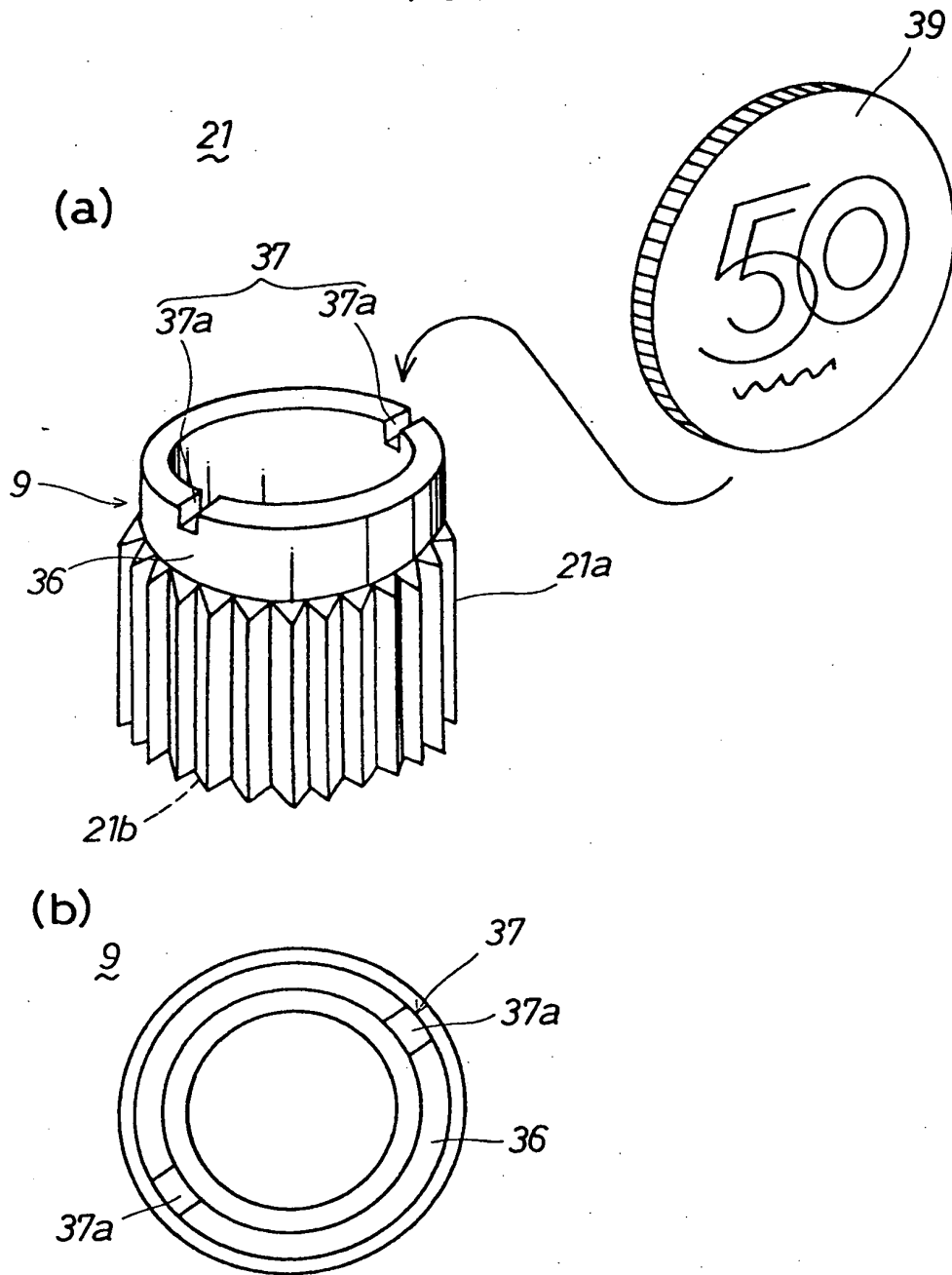


FIG.5



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FIG. 6



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FIG. 7

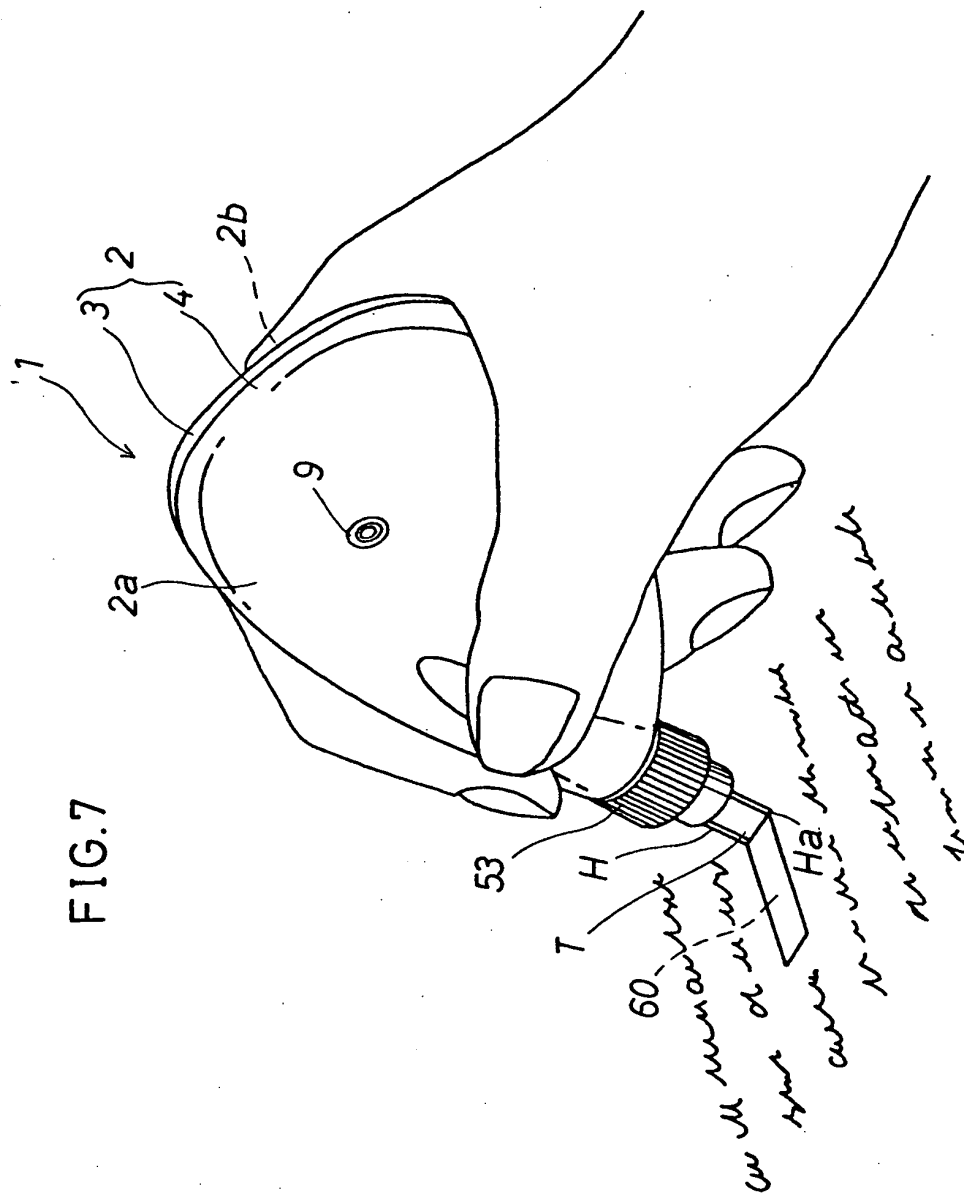
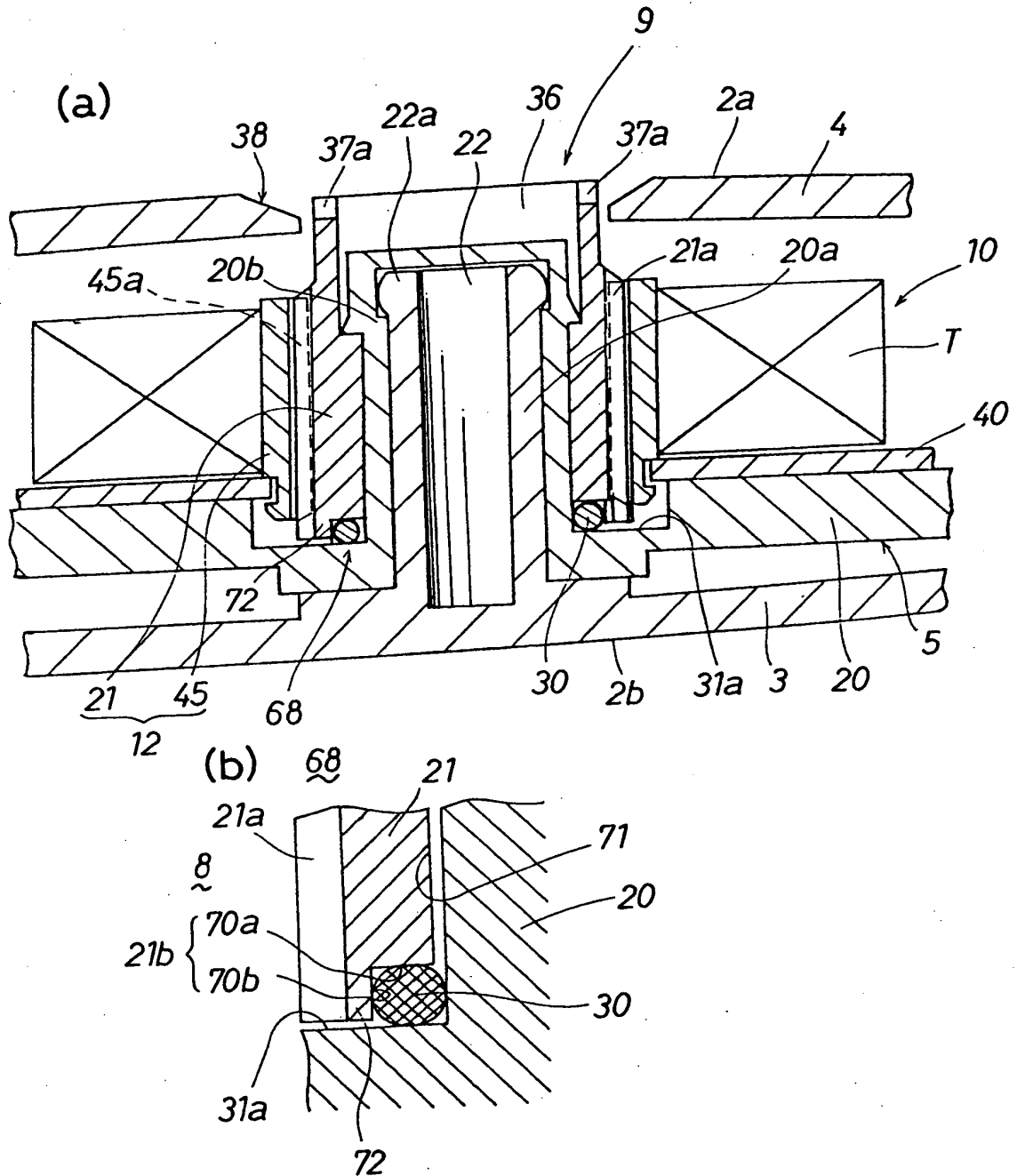


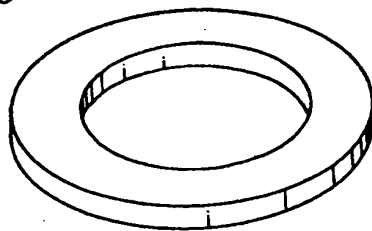
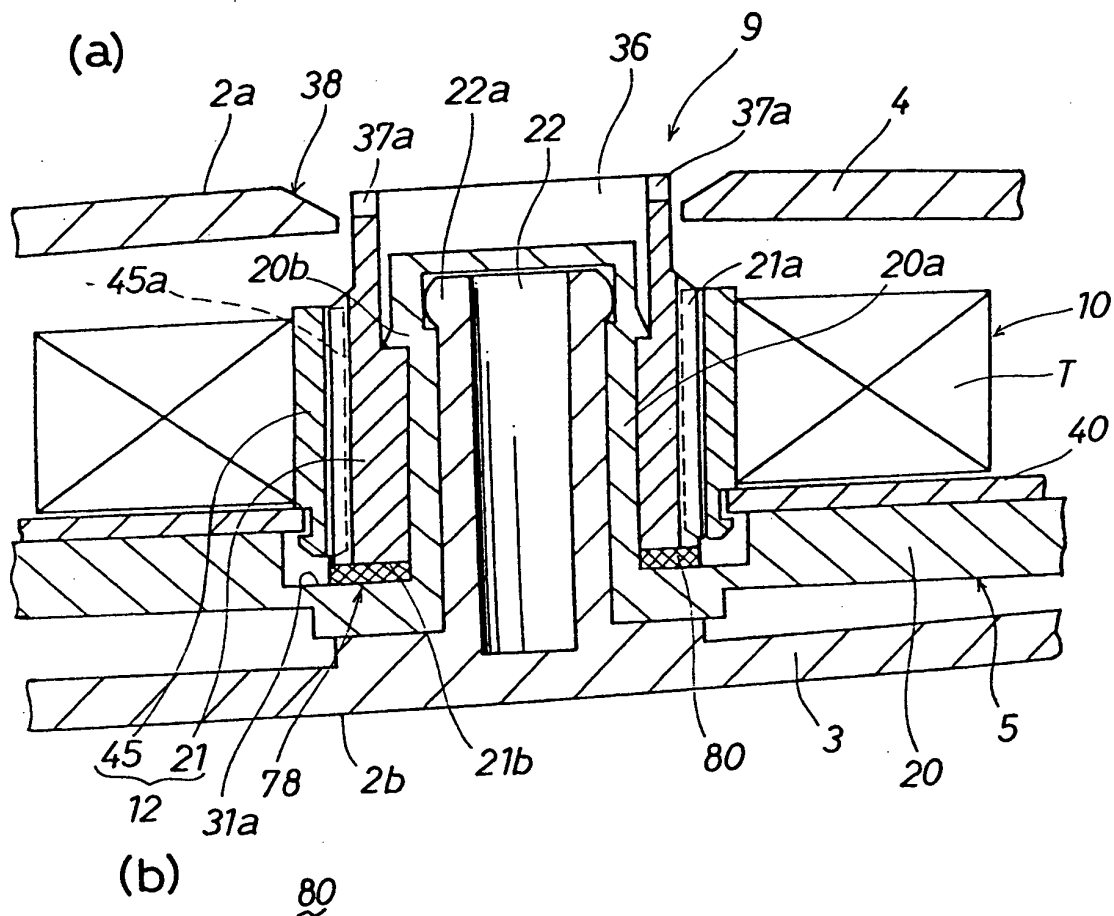
FIG. 8



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FIG. 9





(a) A detailed cross-sectional view of a semiconductor device. The substrate includes layers 9, 4, 10, T, 40, 3, 31, and 5. On top of the substrate are various components: a central core 22 with a vertical channel 36; side structures 20a and 20b; and contact regions 21a and 21b. Other labeled parts include 2a, 38, 37a, 22a, 45a, 20, 45, 21, 100, 98, 99, 2b, and 12.

(b) A top-down circular view of a component 100, showing concentric rings and a central opening. A portion of the outer ring is labeled 100a.

(c) A cross-sectional view of the component 100 from (b), showing its integration with the underlying substrate layers. Labels include 21, 98, 20, 100a, 21a, 100, and 99.



FIG.13

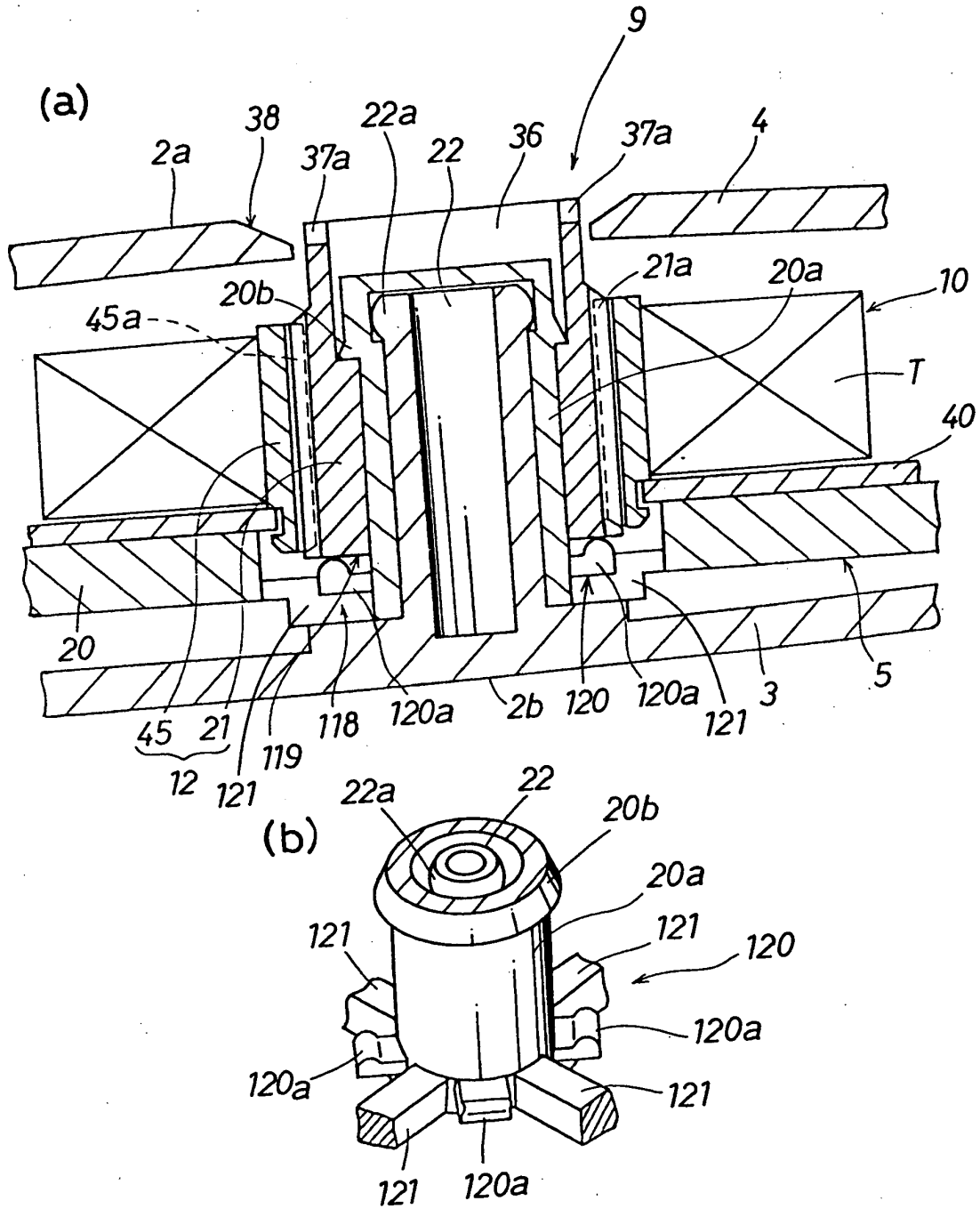
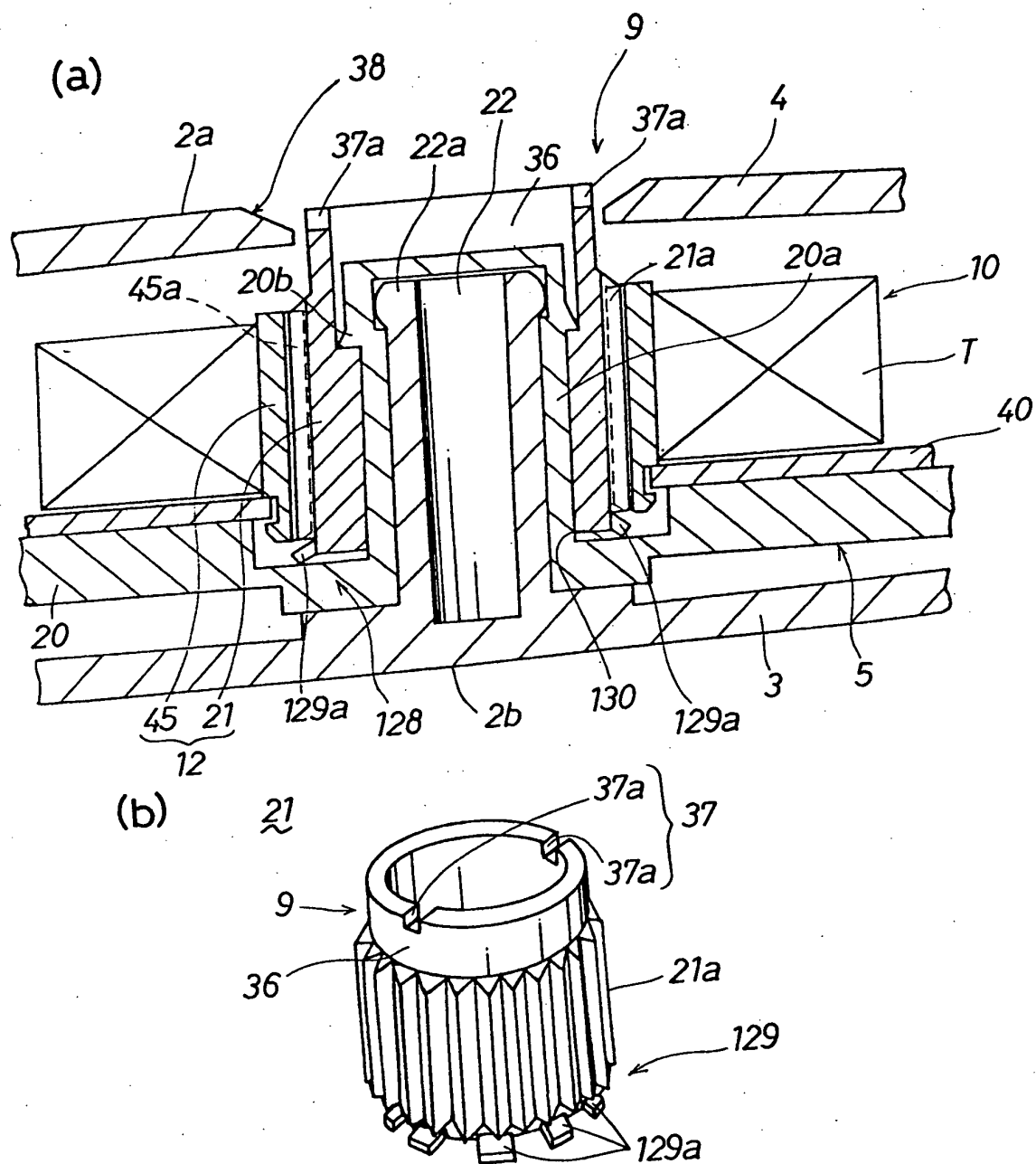


FIG.14





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FIG. 16

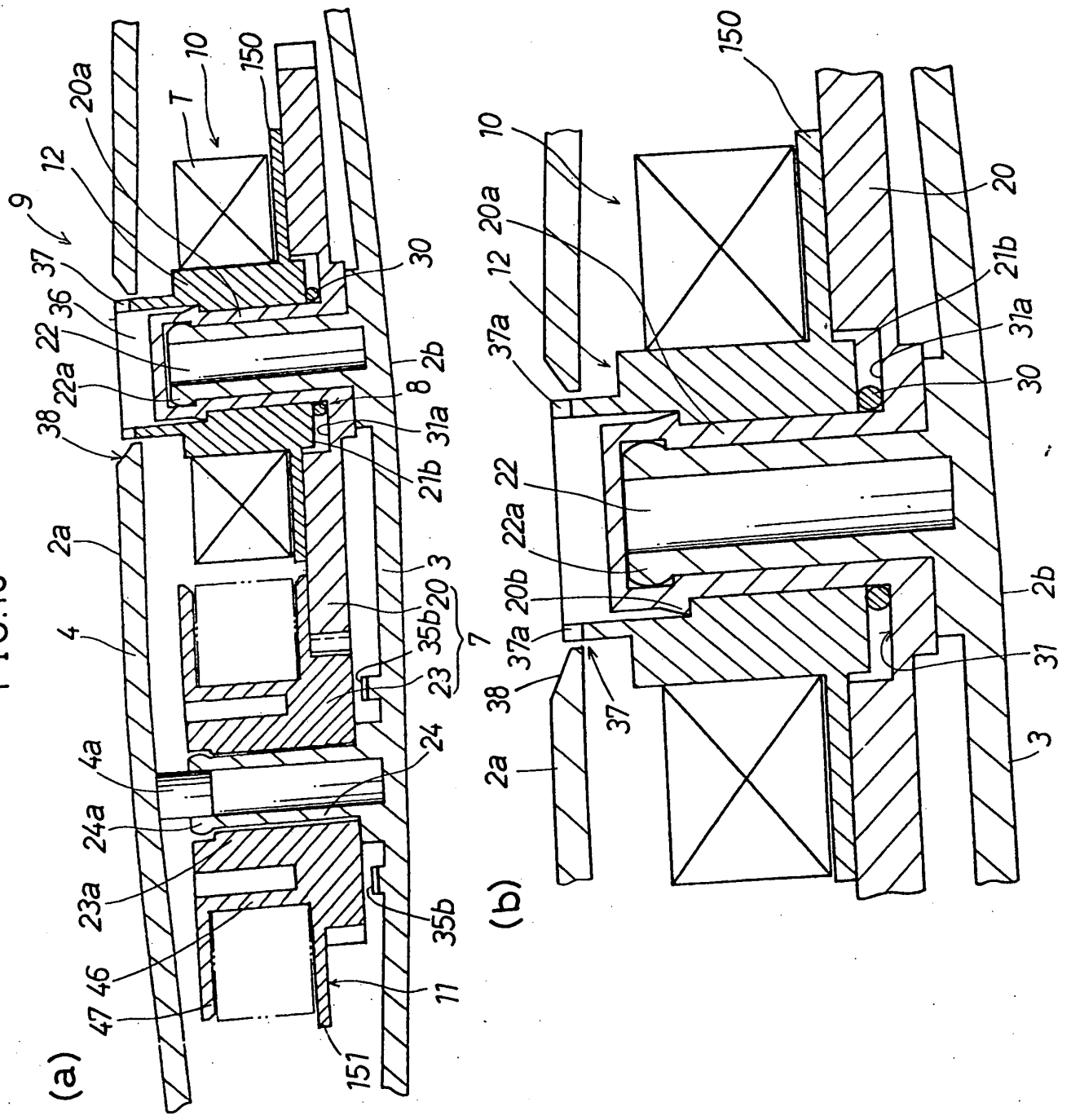
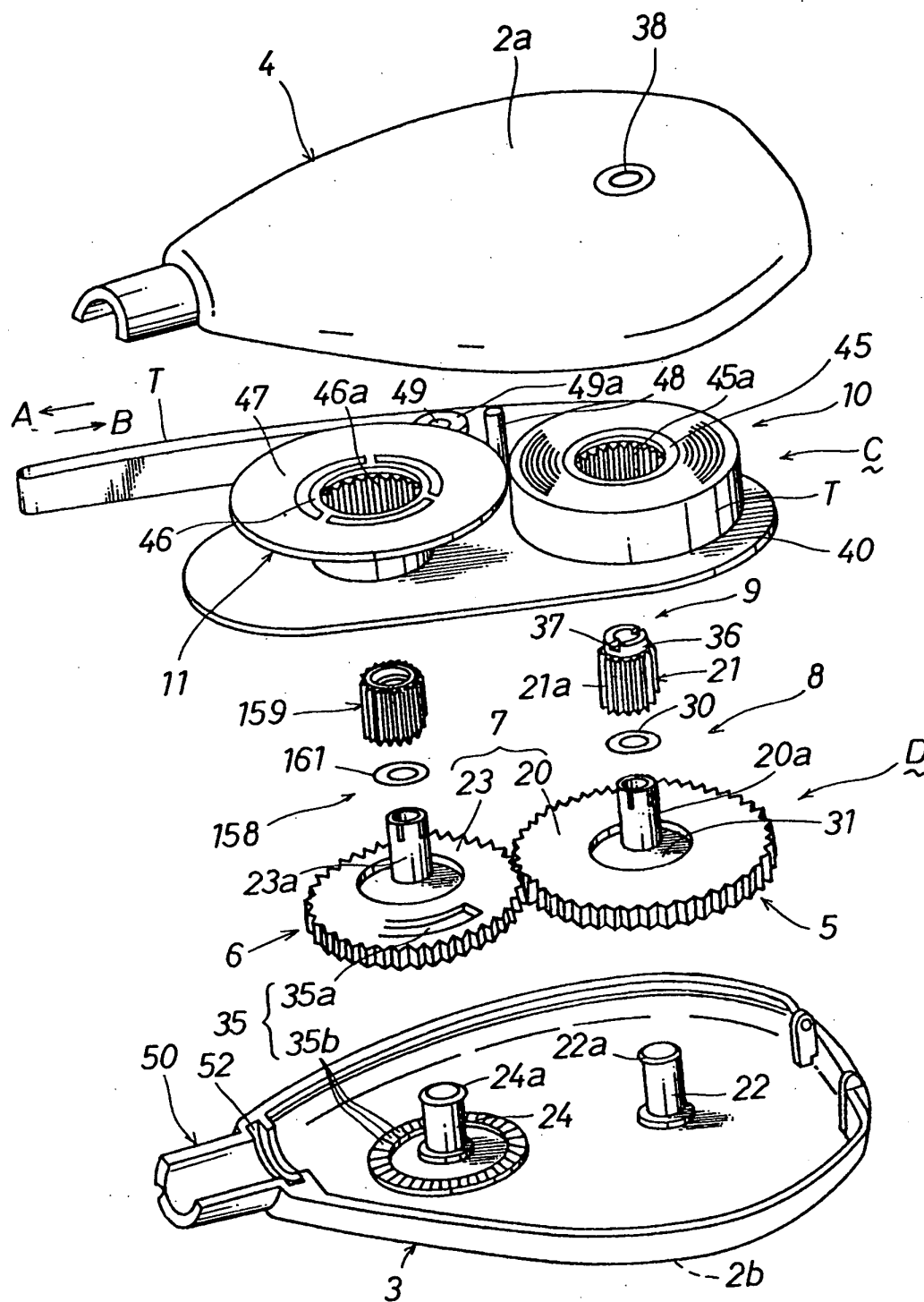






FIG.18



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FIG. 19

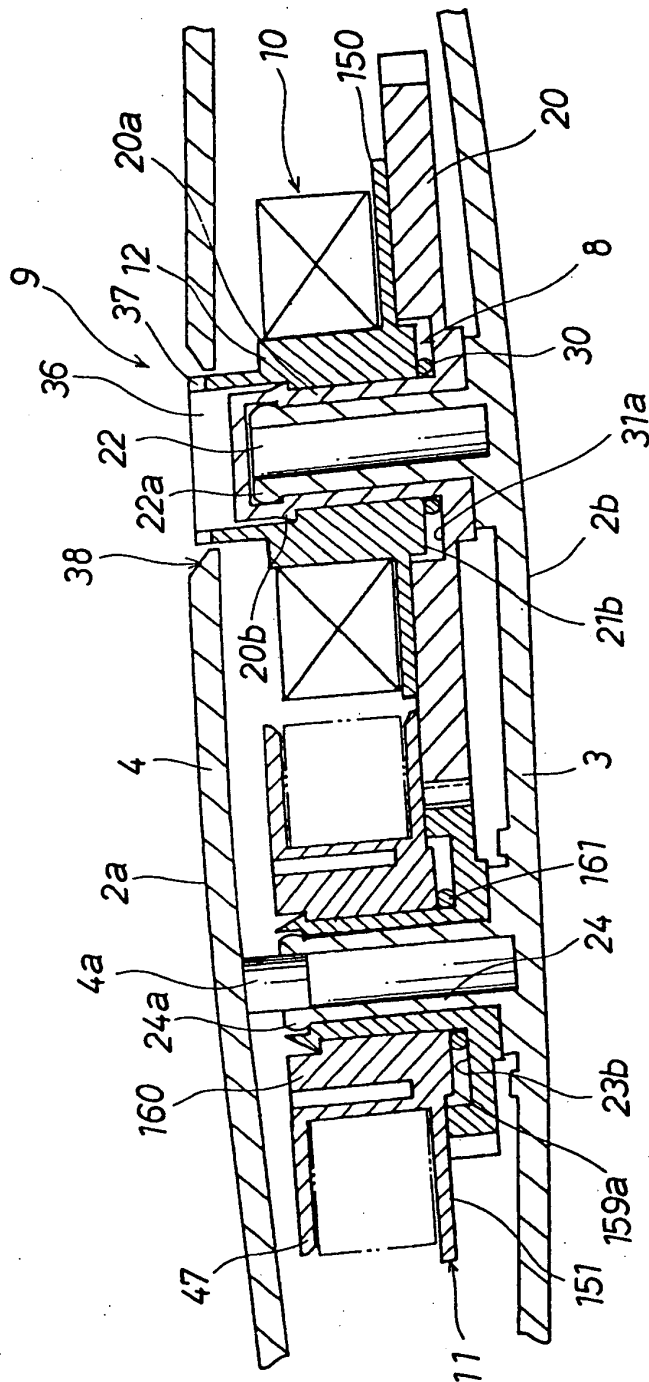
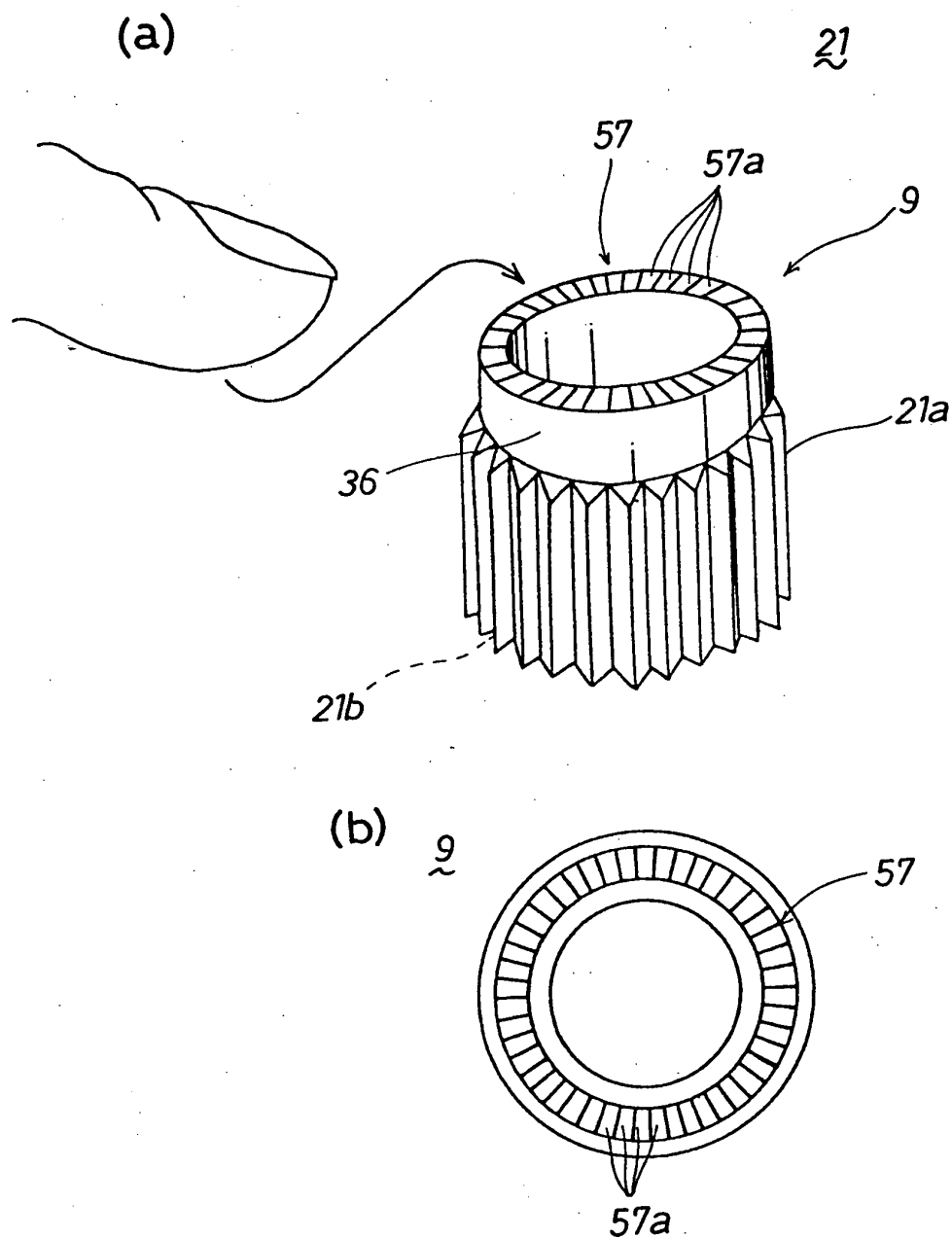
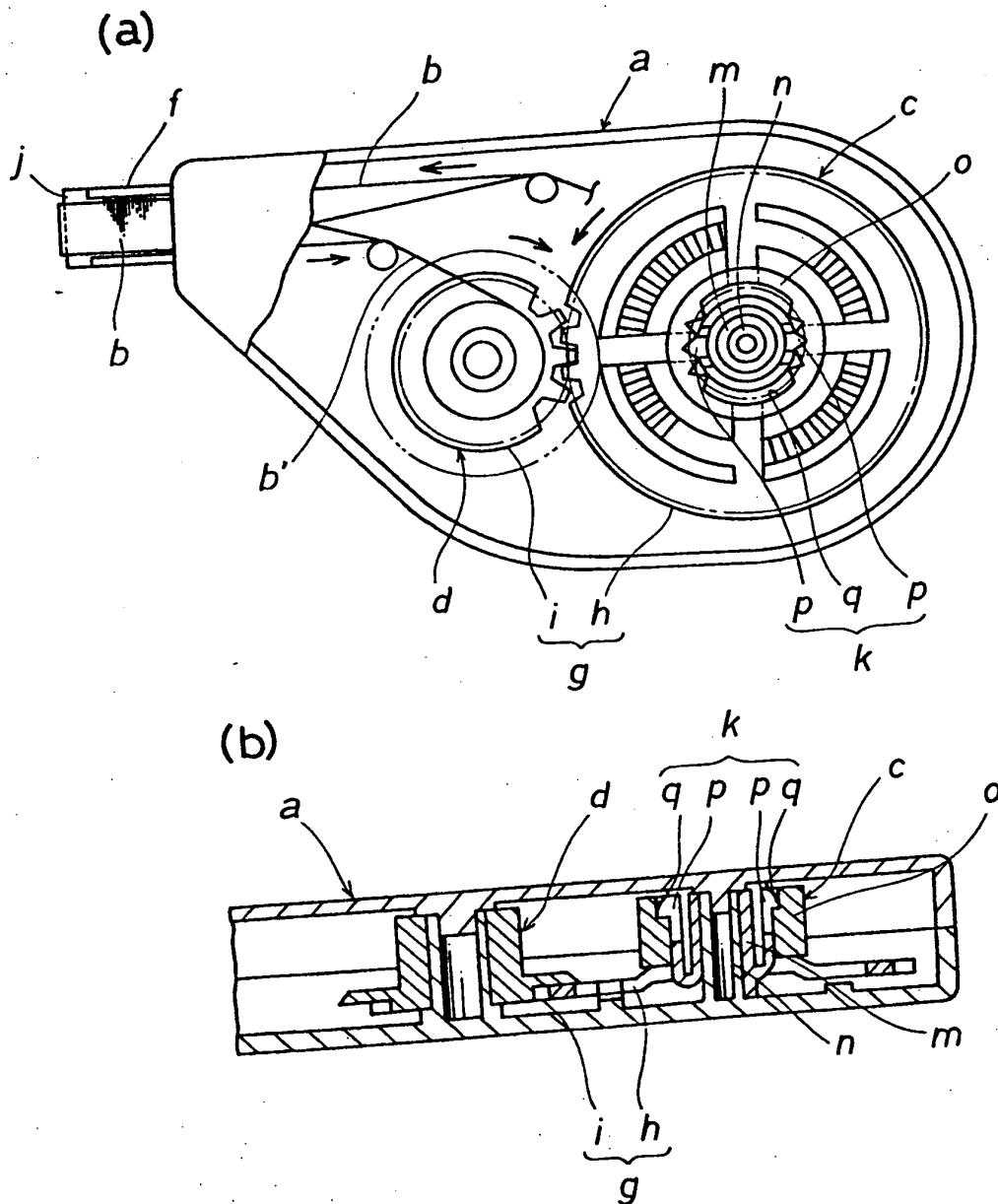


FIG. 20



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FIG. 21



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FIG.22

